

Euijun Cha

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11319497/publications.pdf>

Version: 2024-02-01

13
papers

495
citations

933264

10
h-index

1199470

12
g-index

13
all docs

13
docs citations

13
times ranked

711
citing authors

#	ARTICLE	IF	CITATIONS
1	High Current Density and Nonlinearity Combination of Selection Device Based on TaO _x /TiO ₂ /TaO _x Structure for One Selector-One Resistor Arrays. ACS Nano, 2012, 6, 8166-8172.	7.3	138
2	Comprehensive scaling study of NbO ₂ insulator-metal-transition selector for cross point array application. Applied Physics Letters, 2016, 108, .	1.5	84
3	Multi-layered NiOy/NbOx/NiOy fast drift-free threshold switch with high Ion/Ioff ratio for selector application. Scientific Reports, 2017, 7, 4068.	1.6	59
4	Dynamics of electroforming and electrically driven insulator-metal transition in NbO _x selector. Applied Physics Letters, 2016, 108, .	1.5	42
5	Highly uniform and reliable resistance switching properties in bilayer WO _x /NbO _x RRAM devices. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1179-1183.	0.8	37
6	Control of Cu Conductive Filament in Complementary Atom Switch for Cross-Point Selector Device Application. IEEE Electron Device Letters, 2014, 35, 60-62.	2.2	31
7	Improved switching uniformity in resistive random access memory containing metal-doped electrolyte due to thermally agglomerated metallic filaments. Applied Physics Letters, 2012, 100, .	1.5	27
8	Vertically Stacked ReRAM Composed of a Bidirectional Selector and CB-RAM for Cross-Point Array Applications. IEEE Electron Device Letters, 2013, 34, 1512-1514.	2.2	25
9	Effect of interfacial oxide layer on the switching uniformity of Ge ₂ Sb ₂ Te ₅ -based resistive change memory devices. Applied Physics Letters, 2011, 99, 162109.	1.5	15
10	Multilayer-oxide-based bidirectional cell selector device for cross-point resistive memory applications. Applied Physics Letters, 2013, 103, .	1.5	13
11	Defect Engineering Using Bilayer Structure in Filament-Type RRAM. IEEE Electron Device Letters, 2013, 34, 1250-1252.	2.2	10
12	BEOL compatible (300Å) TiN/TiO _x /Ta/TiN 3D nanoscale ($\sim 10\text{nm}$) IMT selector. , 2013, , .		8
13	Optimized Lightning-Rod Effect to Overcome Trade-Off Between Switching Uniformity and On/Off Ratio in ReRAM. IEEE Electron Device Letters, 2014, 35, 214-216.	2.2	6